

GaAs Broadband SPDT Switch
DC - 6.0 GHz

MASWSS0070
V4

Features

- 802.11a + b/g Dual Band Applications
- Broadband Performance: DC - 6.0 GHz
- Low Insertion Loss: 0.75 dB @ 5.8 GHz
- High Isolation: 22 dB @ 5.8 GHz
- Low Cost 3 mm 12-Lead PQFN Package
- Fast Switching Speed: 0.5 μ m GaAs PHEMT

Description

M/A-COM's MASWSS0070 is a broadband GaAs PHEMT MMIC SPDT switch available in a low cost 3 mm 12-lead PQFN package. The MASWSS0070 is ideally suited for applications where very small size and low cost are required.

Typical applications are for WLAN IEEE 802.11a and 802.11b/g PC cards and access points. Other applications include cordless phones and base stations. Designed for high power, this SPDT switch maintains high linearity up to 6.0 GHz.

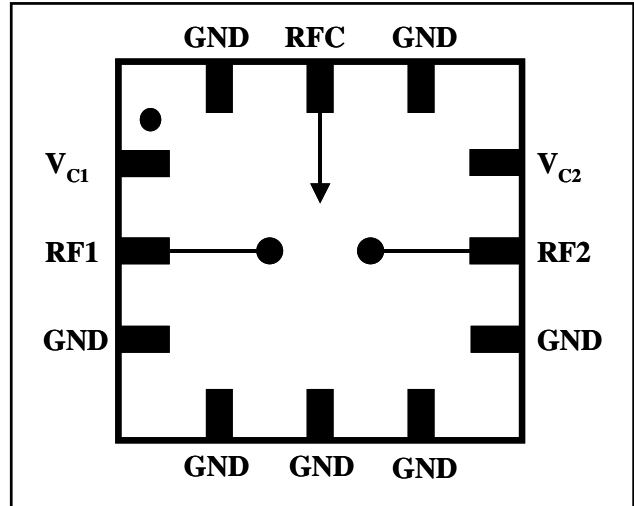
The MASWSS0070 is fabricated using a 0.5 micron gate length GaAs PHEMT process. The process features full passivation for performance and reliability.

Ordering Information ¹

| Part Number | Package |
|-------------------|---|
| MASWSS0070 | Bulk Packaging |
| MASWSS0070TR | 7 inch, 1000 piece reel |
| MASWSS0070TR-3000 | 13 inch, 3000 piece reel |
| MASWSS0070SMB | Sample Test Board (Includes 5 Samples) |

1. Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration

| Pin No. | Pin Name | Description |
|---------|---------------------|------------------|
| 1 | V _{C1} | Control 1 |
| 2 | RF1 | RF Port |
| 3 | GND | Ground |
| 4 | GND | Ground |
| 5 | GND | Ground |
| 6 | GND | Ground |
| 7 | GND | Ground |
| 8 | RF2 | RF Port |
| 9 | V _{C2} | Control 2 |
| 10 | GND | Ground |
| 11 | RFC | RF Port |
| 12 | GND | Ground |
| 13 | Paddle ² | RF and DC Ground |

2. The exposed pad centered on the package bottom must be connected to RF and DC ground.

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Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50 \Omega$, $V_C = 0 \text{ V} / 3 \text{ V}$, 8 pF Capacitor ³

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|-----------------------------|---|---------------|------|------|------|
| Insertion Loss ⁴ | 2 - 3 GHz | dB | — | 0.55 | 0.9 |
| | 3 - 4 GHz | dB | — | 0.55 | 0.9 |
| | 4 - 5 GHz | dB | — | 0.65 | 1.0 |
| | 5 - 6 GHz | dB | — | 0.75 | 1.1 |
| Isolation | 2 - 6 GHz | dB | 22 | 25 | — |
| Return Loss | DC - 6 GHz | dB | — | 20 | — |
| IIP2 | Two Tone, +5 dBm / Tone, 5 MHz Spacing | | | | |
| | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 91 | — |
| | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 5.8 \text{ GHz}$ | dBm | — | 81 | — |
| | $V_C = 0.0 \text{ V} / 5 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 99 | — |
| IIP3 | Two Tone, +5 dBm / Tone, 5 MHz Spacing | | | | |
| | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 52 | — |
| | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 5.8 \text{ GHz}$ | dBm | — | 50 | — |
| | $V_C = 0.0 \text{ V} / 5 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 53 | — |
| Input P-1dB | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 32 | — |
| | $V_C = 0.0 \text{ V} / 3 \text{ V} @ 5.8 \text{ GHz}$ | dBm | — | 29 | — |
| | $V_C = 0.0 \text{ V} / 5 \text{ V} @ 2.4 \text{ GHz}$ | dBm | — | 37 | — |
| | $V_C = 0.0 \text{ V} / 5 \text{ V} @ 5.8 \text{ GHz}$ | dBm | — | 35 | — |
| 2nd Harmonic | 2.4 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -88 | — |
| | 5.3 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -91 | — |
| | 5.8 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -77 | — |
| 3rd Harmonic | 2.4 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -87 | — |
| | 5.3 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -81 | — |
| | 5.8 GHz, $P_{IN} = +20 \text{ dBm}$ | dBc | — | -85 | — |
| T-rise, T-fall | 10% to 90% RF and 90% to 10% RF | nS | — | 13 | — |
| Ton, Toff | 50% control to 90% RF, 50% control to 10% RF | nS | — | 35 | — |
| Transients | | mV | — | 14 | — |
| Control Current | $ V_C = 3 \text{ V}$ | μA | — | 10 | 25 |

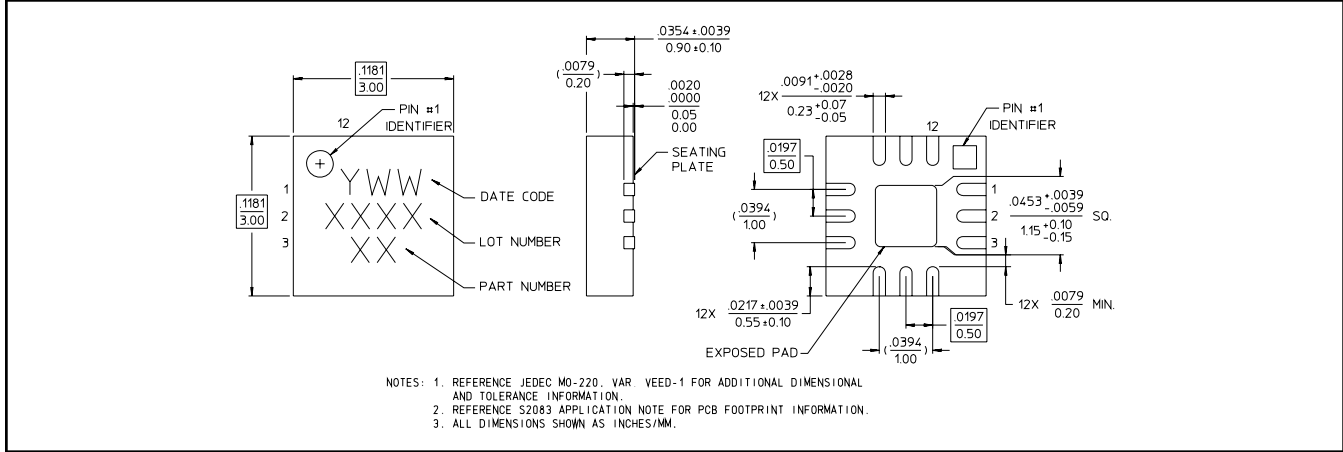
3. For positive voltage control, external DC blocking capacitors are required on all RF ports.

4. Insertion loss can be optimized by varying the DC blocking capacitor value.

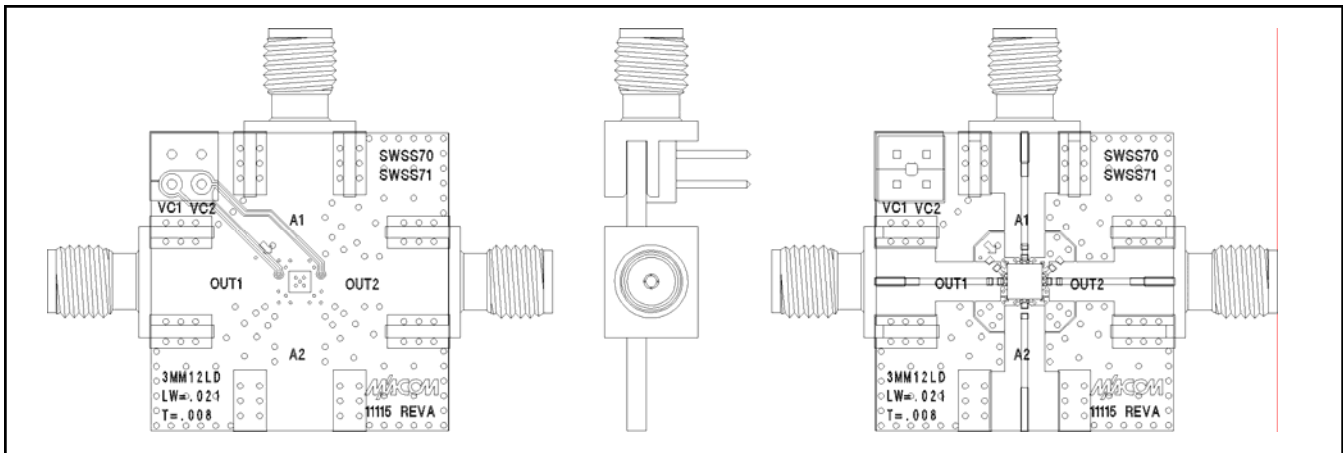
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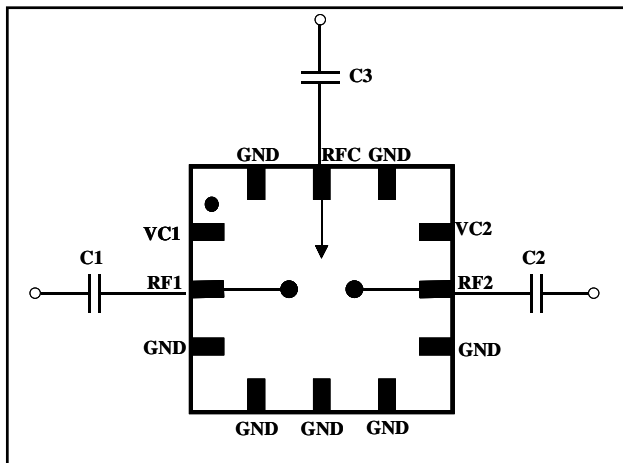
3 mm 12-Lead PQFN



Evaluation Board



Application Schematic



Application #1: Optimized for 802.11a (5-6 GHz)

| Qty | Description |
|-----|--|
| 3 | Capacitor, 3.0 pF, 0402, SMT, 5% (C1-C3) |

Application #2: Optimized for 802.11b/g (2.4 GHz)

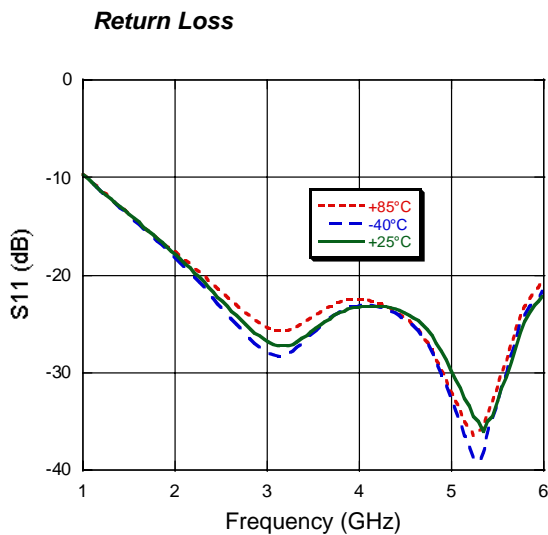
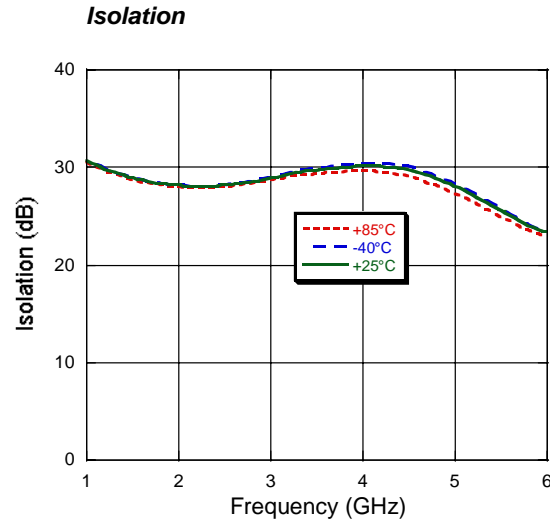
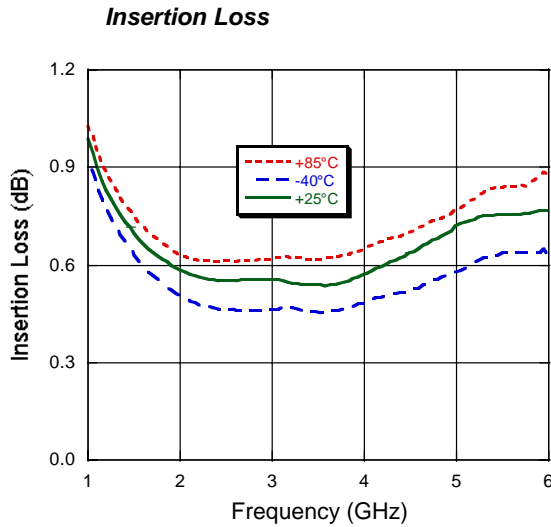
| Qty | Description |
|-----|--|
| 3 | Capacitor, 8.0 pF, 0402, SMT, 5% (C1-C3) |

Truth Table ⁵

| Control V1 | Control V2 | RFC—RF1 | RFC—RF2 |
|------------|------------|---------|---------|
| 1 | 0 | On | Off |
| 0 | 1 | Off | On |

5. 1 = +2.9 V to +5 V, 0 = 0 V ± 0.2 V.

Typical Performance Curves with 0/3 V Control, 8 pF Capacitors



Absolute Maximum Ratings^{6,7}

| Parameter | Absolute Maximum |
|---------------------------|------------------|
| Input Power @ 3 V Control | +32 dBm |
| Input Power @ 5 V Control | +34 dBm |
| Operating Voltage | +8.5 volts |
| Operating Temperature | -40°C to +85°C |
| Storage Temperature | -65°C to +150°C |

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.

Qualification

Qualified to M/A-COM specification REL-201, Process Flow -2.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.